2SK2324(Tentative)

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

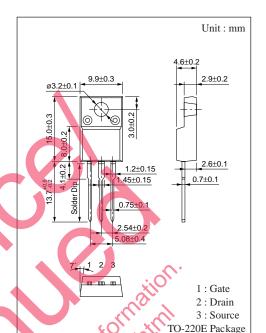
Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings ($Tc = 25^{\circ}C$)

Paramete	Symbol	Rating	Unit		
Drain-Source breakde	V _{DSS}	600	V		
Gate-Source voltage	V _{GSS}	±30	V		
Drain current	DC	I_{D}	±2	A	
	Pulse	I_{DP}	±4	A	
Avalanche energy ca	EAS*	10	mJ		
Allowable power dissipation	$T_C = 25^{\circ}C$ $Ta = 25^{\circ}C$	P_{D}	2 40	W	
Channel temperature		T _{ch}	150	č	
Storage temperature	T _{stg}	-55 to +150	ill C		

Absolute Ma	MITTUITI I LA	ungs(IC	- 23 C)			() ·		3 : Sou
Paramet	ter	Symbol	Rating	Unit		(O) V	TO-22	0E Pacl
Drain-Source breakdown voltage		V _{DSS}	600	V		i ot		
Gate-Source voltag	e	V _{GSS}	±30	V	xes.	200		
Drain current	DC	I_{D}	±2	A	100			
	Pulse	I_{DP}	±4	A	all alle			
Avalanche energy c	apability	EAS*	10	mJ				
Allowable power dissipation	$T_C = 25^{\circ}C$ $Ta = 25^{\circ}C$	P_{D}	2 40	Unit V V A A M W CC III C CO III C	elli			
Channel temperatur	re	T _{ch}	150	£ .'\6\				
Storage temperature	e	Teto	-55 to +150	11,5 Co.,				
Electrical Ch	aracteristic	cs (Tc = 2)	25°C);	asonic.co	76		16	
L= 5mH, I _L = 2A, 1 pulse Electrical Characteristic Parameter Drain-Source cut-off current		Symbol	Condition		Min	Тур	Max	Uı
	ff current	I _{DSS}	V _{DS} = 480V, V					
Gate-Source leakag		- ()	1XV				100	μ
-		IGSS	V _{GS} =± 30V, V	$V_{\rm DS}=0$			100 ±1	
Drain-Source break	down voltage	V _{DSS}	$V_{GS}=\pm 30V, V_{GS}$ $I_D=1$ mA, V_{GS}	$V_{\rm DS} = 0$ $= 0$	600			 '
Drain-Source breakd Gate threshold volt	lown voltage age	IGSS	V _{GS} =± 30V, V	$V_{\rm DS} = 0$ $= 0$	600			Ļ
Drain-Source break	lown voltage age	V _{DSS}	$V_{GS}=\pm 30V, V_{GS}$ $I_D=1$ mA, V_{GS}	V _{DS} = 0 = 0 =1mA		4.9	±1	
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit	lown voltage age esistance	VDSS Vth RDS(on)	$V_{GS}=\pm 30V$, $V_{DS}=1$ mA, V_{GS} $V_{DS}=25V$, I_{D}	V _{DS} = 0 = 0 =1mA		4.9	±1 5	
Drain-Source breakd Gate threshold voltd Drain-Source ON-r Forward transadmit Diode forward voltd	lown voltage age esistance	V _{DSS} V _{th} R _{DS(on)}	V_{GS} =± 30V, V I_D =1mA, V_{GS} V_{DS} = 25V, I_D V_{GS} =10V, I_D =	V _{DS} = 0 = 0 =1mA =1A	2		±1 5	
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance	lown voltage age esistance ttance age	I ₆ 88 V _{DSS} V _{th} R _{DS(on)} Y _{fs} V _{DSF} C _{iss}	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=10M, V_{$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0	2		±1 5 6	Ļ
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance Output capacitance	down voltage age esistance ttance age	I ₆ SS	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=10M, V_{$	V _{DS} = 0 = 0 =1mA =1A	2	0.85	±1 5 6	
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance	down voltage age esistance ttance age	I ₆ 88 V _{DSS} V _{th} R _{DS(on)} Y _{fs} V _{DSF} C _{iss}	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=10M, V_{$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0	2	0.85 260	±1 5 6	ŀ
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance Output capacitance	down voltage age esistance stance age	VDSS Vth RDS(on) Yfs VDSF Ciss Coss	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=10M, V_{$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0	2	0.85 260 35	±1 5 6	ŀ
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance Output capacitance Feedback capacitan	down voltage age esistance stance age	VDSS Vth RDS(on) Yfs VDSF Ciss Coss Crss	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=10M, V_{$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0 = 0	2	0.85 260 35 10	±1 5 6	ŀ
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance Output capacitance Feedback capacitan Turn-on time (delay	down voltage age esistance stance age	I ₆ SS	$V_{GS}=\pm 30V, V_{GS}=10M, V_{GS}=10M, V_{GS}=10V, I_{D}=10M, V_{DS}=25V, I_{D}=10M, V_{DS}=25V, V_{DS}=2M, V$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0 = 0 = 0 = 0 = 1MHz	2	0.85 260 35 10 15	±1 5 6	ŀ
Drain-Source breakd Gate threshold volt Drain-Source ON-r Forward transadmit Diode forward volt Input capacitance Output capacitance Feedback capacitan Turn-on time (delay Rise time	down voltage age esistance stance age	$\begin{tabular}{ll} I_{GSS} & V_{DSS} & V_{th} & $R_{DS(on)}$ & $ Y_{fs} $ & V_{DSF} & C_{iss} & C_{oss} & C_{rss} & $t_{d(on)}$ & t_r & $t_$	$V_{GS}=\pm 30V, V_{ID}=1mA, V_{GS}$ $V_{DS}=25V, I_{D}$ $V_{GS}=10V, I_{D}=$ $V_{DS}=25V, I_{D}$ $I_{DR}=2A, V_{GS}$ $V_{DS}=20V, V_{C}$ $V_{DD}=200V, I_{D}=$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0 = 0 = 0 = 0 = 1MHz	2	0.85 260 35 10 15 25	±1 5 6	ŀ
Drain-Source breakd Gate threshold volts Drain-Source ON-r Forward transadmit Diode forward volts Input capacitance Output capacitance Feedback capacitant Turn-on time (delay Rise time	down voltage age esistance ttance age age vtime)	$\begin{tabular}{ll} I_{GSS} & V_{DSS} & V_{th} & $R_{DS(on)}$ & $ Y_{fs} $ & V_{DSF} & C_{iss} & C_{oss} & C_{rss} & $t_{d(on)}$ & t_r & t_f & $t_$	$V_{GS}=\pm 30V, V_{ID}=1mA, V_{GS}$ $V_{DS}=25V, I_{D}$ $V_{GS}=10V, I_{D}=$ $V_{DS}=25V, I_{D}$ $I_{DR}=2A, V_{GS}$ $V_{DS}=20V, V_{C}$ $V_{DD}=200V, I_{D}=$	V _{DS} = 0 = 0 = 1mA = 1A = 1A = 0 = 0 = 0 = 0 = 1MHz	2	0.85 260 35 10 15 25 35	±1 5 6	ŀ



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